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November 2013

## **FDP33N25**

# N-Channel UniFET<sup>TM</sup> MOSFET 250 V, 33 A, 94 m $\Omega$

#### **Features**

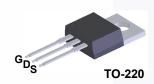
- $R_{DS(on)}$  = 94  $m\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 16.5 A
- Low Gate Charge (Typ. 36.8 nC)
- Low C<sub>rss</sub> (Typ. 39 pF)
- · 100% Avalanche Tested

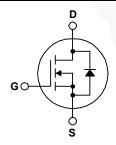
## **Applications**

- PDP TV
- Lighting
- · Uninterruptible Power Supply
- AC-DC Power Supply

## **Description**

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





## **Absolute Maximum Ratings** T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		FDP33N25	Unit	
$V_{DSS}$	Drain-Source Voltage		250	V
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)	33 20.4	A A
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)	132	Α
V <sub>GSS</sub>	Gate-Source voltage	± 30	V	
E <sub>AS</sub>	Single Pulsed Avaland	che Energy (Note 2)	918	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	33	Α
E <sub>AR</sub>	Repetitive Avalanche Energy (Note		23.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
$P_D$	Power Dissipation	(T <sub>C</sub> = 25°C) - Derate Above 25°C	235 1.89	W/°C
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storag	e Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temp	erature for Soldering, 1/8" from Case for 5 Seconds	300	°C

### **Thermal Characteristics**

Symbol	Parameter	FDP33N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.53	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	C/VV

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP33N25	FDP33N25	TO-220	Tube	N/A	N/A	50 units

## **Electrical Characteristics** $T_C = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions		Тур	Max	Unit
Off Charac	cteristics			•	•	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V, } I_D = 250  \mu\text{A, } T_J = 25^{\circ}\text{C}$	250			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.25		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V V <sub>DS</sub> = 200 V, T <sub>C</sub> = 125°C			1 10	μA μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Charac	teristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16.5 A		0.077	0.094	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 16.5 A		26.6		S
Dynamic C	Characteristics			•	•	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		1640	2135	pF
C <sub>oss</sub>	Output Capacitance			330	430	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			39	59	pF
Switching	Characteristics				•	
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD}$ = 125 V, $I_{D}$ = 33 A, $V_{GS}$ = 10 V, $R_{G}$ = 25 $\Omega$ (Note 4)		35	80	ns
t <sub>r</sub>	Turn-On Rise Time			230	470	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			75	160	ns
t <sub>f</sub>	Turn-Off Fall Time			120	250	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 200 V, I <sub>D</sub> = 33 A,		36.8	48	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		10		nC
Q <sub>gd</sub>	Gate-Drain Charge (Note 4)			17		nC
Drain-Sou	rce Diode Characteristics and Maximur	n Ratings				
Is	Maximum Continuous Drain-Source Diode Forward Current				33	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				132	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 33 A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 33 A,		220		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> /dt =100 A/μs		1.71		μС

#### Notes

 $<sup>{\</sup>it 1. Repetitive\ rating: pulse-width\ limited\ by\ maximum\ junction\ temperature.}$ 

<sup>2.</sup> L = 1.35 mH, I  $_{AS}$  = 33 A, V  $_{DD}$  = 50 V, R  $_{G}$  = 25  $\Omega,$  starting T  $_{J}$  = 25  $^{\circ}C.$ 

<sup>3.</sup> I  $_{SD} \leq$  33 A, di/dt  $\leq$  200 A/µs, V  $_{DD} \leq$  BV  $_{DSS},$  starting T  $_{J}$  = 25°C.

<sup>4.</sup> Essentially independent of operating temperature typical characteristics.

## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

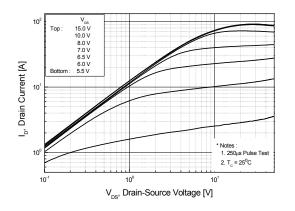
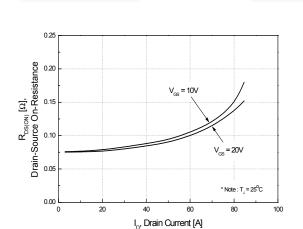


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage



**Figure 5. Capacitance Characteristics** 

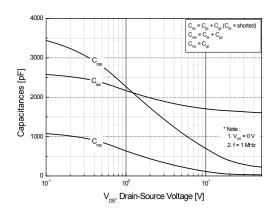


Figure 2. Transfer Characteristics

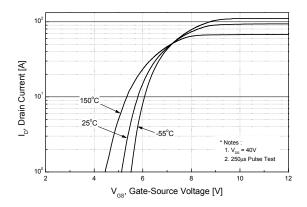
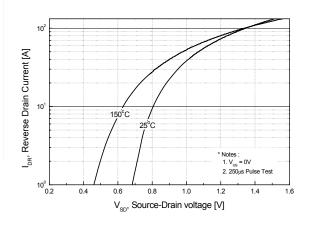
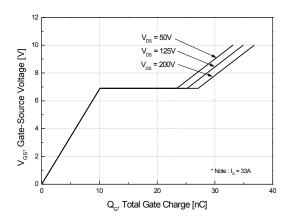


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue



**Figure 6. Gate Charge Characteristics** 



## Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

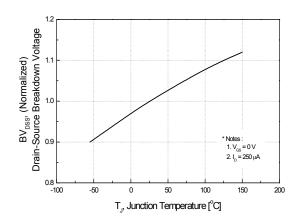


Figure 8. On-Resistance Variation vs. Temperature

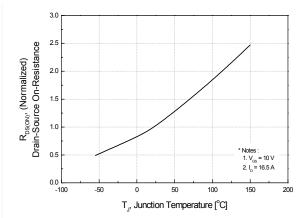


Figure 9. Maximum Safe Operating Area

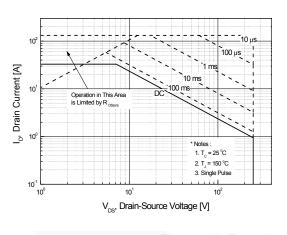


Figure 10. Maximum Drain Current vs. Case Temperature

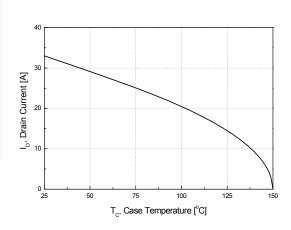
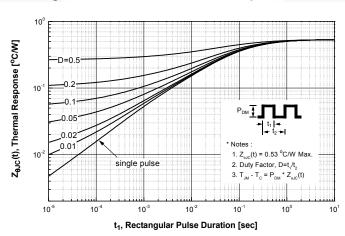


Figure 11. Transient Thermal Response Curve



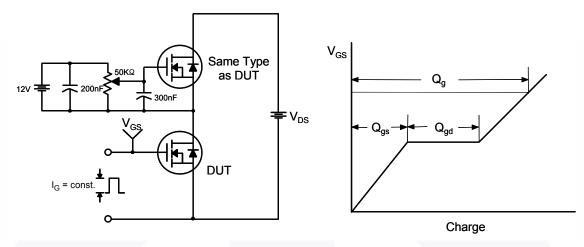


Figure 12. Gate Charge Test Circuit & Waveform

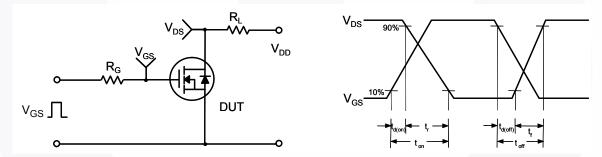


Figure 13. Resistive Switching Test Circuit & Waveforms

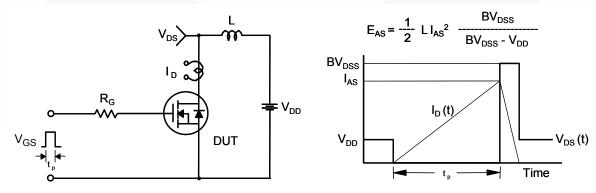


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

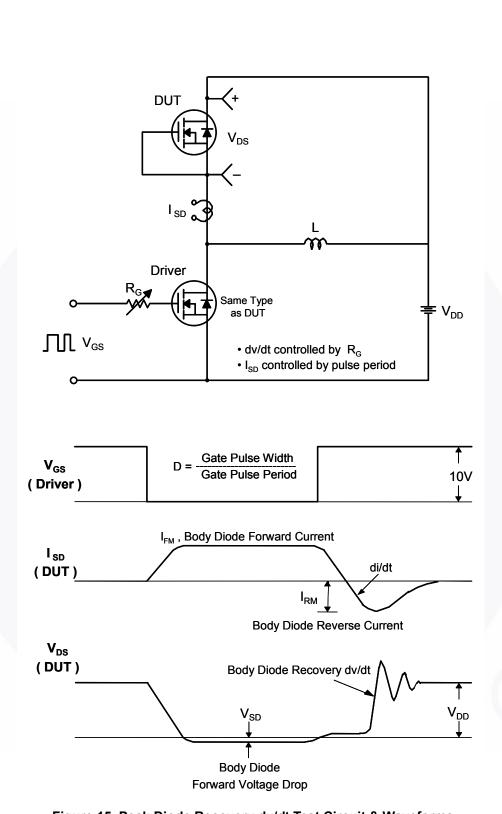


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

### **Mechanical Dimensions**

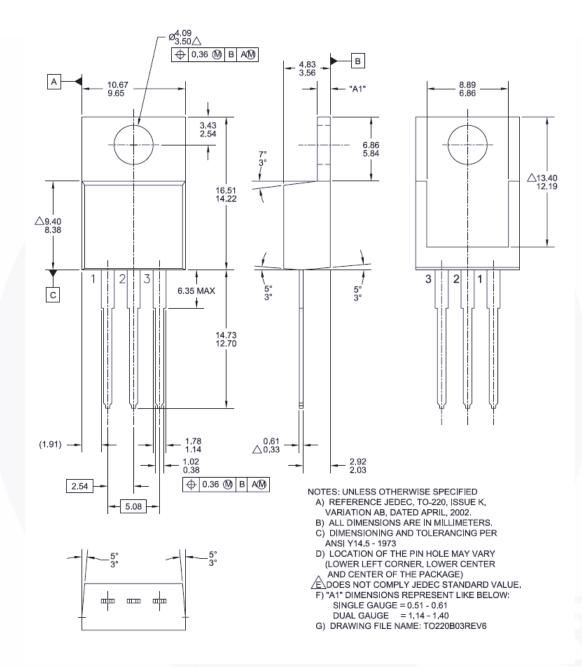


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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